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(54) **RESIN SEALED SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING THE SAME**

(57) A semiconductor chip (15) is bonded on a die pad (13) of a leadframe, and inner leads (12) are electrically connected to electrode pads of the semiconductor chip (15) with metal fine wires (16). The die pad (13), semiconductor chip (15) and inner leads are molded with a resin encapsulant (17). However, no resin encapsulant (17) exists on the respective back surfaces of the inner leads (12), which protrude downward from the back surface of the resin encapsulant (17) so as to be external electrodes (18). That is to say, since the external electrodes (18) protrude, a standoff height can be secured in advance for the external electrodes (18) in bonding the external electrodes (18) to electrodes of a motherboard. Thus, the external electrodes (18) may be used as external terminals as they are, and no ball electrodes of solder or the like need to be provided for the external electrodes (18). Accordingly, this process is advantageous in terms of the number of manufacturing process steps and the manufacturing costs.

Fig. 1(a)

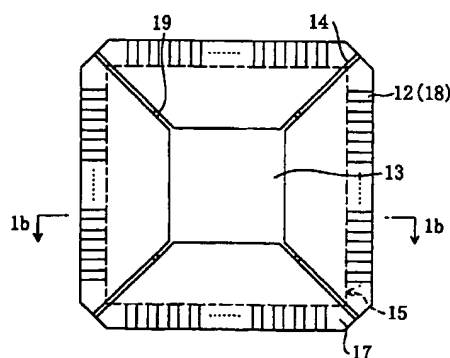
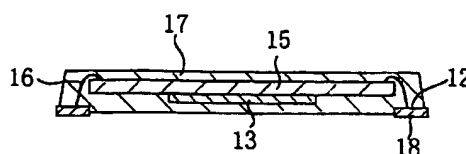


Fig. 1(b)



Description

TECHNICAL FIELD

[0001] The present invention relates to a resin-molded semiconductor device, in which a semiconductor chip and a leadframe are molded with a resin encapsulant, and to a method for manufacturing such a device. In particular, the present invention relates to a device with the back surface of the leadframe partially exposed out of the resin encapsulant.

BACKGROUND ART

[0002] In recent years, in order to catch up with rapidly advancing downsizing of electronic units, it has become increasingly necessary to package semiconductor components for each of these electronic units at a higher and higher density. Correspondingly, sizes and thicknesses of semiconductor components have also been noticeably reduced.

[0003] Hereinafter, a conventional resin-molded semiconductor device will be described.

[0004] Figure 23(a) is a plan view of a conventional resin-molded semiconductor device, and Figure 23(b) is a cross-sectional view of the conventional resin-molded semiconductor device.

[0005] As shown in Figures 23(a) and 23(b), this conventional resin-molded semiconductor device is of the type including external electrodes on its back surface.

[0006] The conventional resin-molded semiconductor device includes a leadframe consisting of: inner leads 201; a die pad 202; and support leads 203 for supporting the die pad 202. A semiconductor chip 204 is bonded onto the die pad 202 with an adhesive, and electrode pads (not shown) of the semiconductor chip 204 are electrically connected to the inner leads 201 with metal fine wires 205. And the die pad 202, semiconductor chip 204, inner leads 201, support leads 203 and metal fine wires 205 are molded with a resin encapsulant 6. In this structure, no resin encapsulant 206 exists on respective back surfaces of the inner leads 201. In other words, the respective back surfaces of the inner leads 201 are exposed and respective lower parts of the inner leads 201, including these exposed back surfaces, serve as external electrodes 207.

[0007] In such a resin-molded semiconductor device, the respective back surfaces of the resin encapsulant 206 and those of the inner leads 201 are both located in the same plane, and the die pad 202 is located above the inner leads 201. That is to say, by providing depressed portions 208 for the support leads 203, the die pad 202 is elevated above the inner leads 201. Thus, after the device has been molded with the resin encapsulant 206, a thin layer of the resin encapsulant 206 is also formed on the back surface of the die pad 202. In Figure 23(a), the resin encapsulant 206 is illustrated as being transparent such that the inside of the

semiconductor device can be looked through. In Figure 23(a), the semiconductor chip 204 is indicated by the dashed line and the illustration of the metal fine wires 205 is omitted.

[0008] Also, conventionally, to secure a required standoff height from the back surface of the resin encapsulant 206 in bonding the external electrodes to the electrodes of a motherboard such as a printed wiring board, on which a resin-molded semiconductor device is mounted, ball electrodes 209 of solder are attached to the external electrodes 207 as shown in Figure 24. After the standoff height has been secured by these ball electrodes 209, the device is mounted onto the motherboard.

[0009] Hereinafter, a method for manufacturing the conventional resin-molded semiconductor device will be described with reference to the drawings. Figures 25 through 27 are cross-sectional views illustrating a manufacturing process for the conventional resin-molded semiconductor device.

[0010] First, as shown in Figure 25, a leadframe 210, including the inner leads 201 and die pad 202, is prepared. It is noted that the die pad 202 is actually supported by the support leads, but the illustration of the support leads is omitted in Figure 25. Depressed portions are formed in the support leads and the die pad 202 is elevated above the plane on which the inner leads 201 are located. The leadframe 210 does not include any tie bar used for preventing the resin encapsulant from flowing out during resin encapsulation.

[0011] Next, as shown in Figure 26, the semiconductor chip 204 is bonded, with an adhesive, to the die pad 202 of the lead-frame prepared. This process step is called "die bonding".

[0012] Then, as shown in Figure 27, the semiconductor chip 204, which has been bonded onto the die pad 202, is electrically connected to the inner leads 201 via the metal fine wires 205. This process step is called "wire bonding". As the metal fine wires 205, aluminum (Al) or gold (Au) fine wires may be appropriately used, for example.

[0013] Subsequently, as shown in Figure 28, the die pad 202, semiconductor chip 204, inner leads 201, support leads and metal fine wires 205 are molded with the resin encapsulant 206. In this case, the leadframe, on which the semiconductor chip 204 has been bonded, is introduced into a molding die assembly and transfer-molded. In particular, resin encapsulation is performed with the back surface of the inner leads 201 in contact with an upper or lower die of the die assembly.

[0014] Finally, the ends 211 of the inner leads 201, protruding outward from the resin encapsulant 206, are cut off after the resin encapsulation. By performing this cutting process step, the end faces of the inner leads 201 cut off are substantially flush with the side faces of the resin encapsulant 6 and the respective lower parts of the inner leads 201 are used as external electrodes 207.

[0015] In the manufacturing process of this conventional resin-molded semiconductor device, the resin encapsulant 206 might overflow from the edges of the inner leads 201, reach the back surfaces thereof and thereby form resin bur thereon (overflowing resin) during the resin encapsulation process step. Thus, a water jet process step is introduced for blowing off the resin bur after the resin encapsulation process step and before the process step of cutting off the inner leads 201.

[0016] Also, if necessary, ball electrodes of solder are formed on the lower surfaces of the external electrodes 207, thereby completing the resin-molded semiconductor device shown in Figure 24. As another alternative, a solder plating layer is sometimes formed instead of the solder balls.

—PROBLEMS TO BE SOLVED—

[0017] The conventional resin-molded semiconductor device, however, has the following drawbacks. First, since the lower surfaces of the external electrodes 207 are located in substantially the same plane as that of the resin encapsulant 206 on the back of the semiconductor device, no standoff height from the resin encapsulant 206 can be obtained. Thus, the device must be mounted onto a motherboard with the ball electrodes 209 of solder interposed therebetween. Accordingly, mounting cannot be carried out efficiently.

[0018] In addition, during the resin encapsulation step of the conventional process for manufacturing a resin-molded semiconductor device, a leadframe, on which a semiconductor chip has been bonded, is introduced into a molding die assembly and then molded with a resin by pressing the inner leads against the surface of the lower die such that the leads closely contact the die. Even so, there occurs a problem that the resin encapsulant reaches the back surface of the inner leads to form a resin bur (overflowing resin) on the surface of the external electrodes.

[0019] Figure 30 is a partial plan view illustrating, on a larger scale, the external electrodes 207 and their surroundings on the back of the semiconductor device as illustrated within the circle in Figure 23(a). As shown in Figure 30, resin bur 206a is sometimes formed on the respective lower surfaces of the external electrodes 207 during the conventional resin encapsulation process step. That is to say, the resin encapsulant 206 reaches the lower surfaces of the external electrodes 207 to form the resin bur 206a thereon during the resin encapsulation process step. In other words, part of each external electrode 207 is buried within the resin encapsulant 206.

[0020] Thus, a water jet process step has heretofore been introduced to blow off the resin bur 206a on the external electrodes 207. However, such a water jet process step is very troublesome and is contradictory to the demand on a process simplification to manufacture

resin-molded semiconductor devices in high volume or on a reduction in number of process steps. That is to say, the formation of the resin bur is a non-negligible factor interfering with such simplification of manufacturing process.

[0021] A leadframe for a general-purpose resin-molded semiconductor device currently used is ordinarily made of copper (Cu) or Alloy 42. This material is plated with nickel (Ni) as an undercoat layer and then plated with palladium (Pd) and gold (Au). In the conventional process, however, if the resin bur is blown off with high-pressure water jet during the water jet process step introduced to remove the resin bur, then not only the resin bur, but also soft metal plating peel off with the water jet. Also, serious quality control problems, like deposition of impurities, might happen.

[0022] To avoid this problem, various measures can be taken, e.g., the leadframe may be plated after the water jet process step is over. However, in such a case, a metal layer pre-plating treatment (or a preparatory plating treatment) cannot be performed, i.e., the leadframe cannot be plated prior to the resin encapsulation process step. Accordingly, the plating process step cannot be performed efficiently, thus further interfering with the simplification of manufacturing process. Also, such a measure is not preferable in terms of the reliability of a resin-molded semiconductor device, either.

[0023] An object of this invention is providing a resin-molded semiconductor device and a method for manufacturing the same, which can meet the demand on a simplified manufacturing process by suppressing the formation of resin bur on the back of a leadframe or by ensuring a standoff height of external electrodes from a resin encapsulant during a resin encapsulation process step.

DISCLOSURE OF INVENTION

[0024] In order to achieve this object, the present invention discloses a resin-molded semiconductor device formed by using a seal tape for preventing the overflow of a resin during resin encapsulation and a method for manufacturing a resin-molded semiconductor device using a seal tape.

[0025] A resin-molded semiconductor device according to the present invention includes: a semiconductor chip having electrode pads; inner leads; connection members for electrically connecting the electrode pads of the semiconductor chip to the inner leads; and a resin encapsulant for molding the semiconductor chip, inner leads and connection members together. The lower part of each said inner lead, including at least part of the back surface thereof, functions as an external electrode. And the external electrode protrudes downward from the back surface of the resin encapsulant.

[0026] In this structure, since the external electrode of the inner lead protrudes from the resin encapsulant, a standoff height can be secured for the external elec-

trode. That is to say, in this structure, the inner leads can be directly connected, as external terminals, onto a motherboard without providing any ball electrodes for the external electrodes. As a result, the first object is accomplished.

[0027] The resin-molded semiconductor device may further include: a die pad for supporting the semiconductor chip thereon; and support leads for supporting the die pad. Each said support lead may include a depressed portion for elevating the die pad above the inner leads.

[0028] In such an embodiment, the resin encapsulant exists under the die pad, thus increasing the force of the resin encapsulant holding the die pad and semiconductor chip. In addition, since the die pad is slightly elevated only by the depth of the depression of the support leads, the structure of the resin-molded semiconductor device can be kept thin without increasing the thickness of the resin-molded semiconductor device so much.

[0029] In the resin-molded semiconductor device, a protrusion height of the external electrodes as measured from the back surface of the resin encapsulant is preferably in the range from about 10 μm to about 40 μm .

[0030] In such an embodiment, the force of the resin encapsulant holding the inner leads is not weakened so much and the external electrodes can be made to function as external terminals.

[0031] A basic method for manufacturing a resin-molded semiconductor device according to the present invention includes: a first step of preparing molding die assembly, semiconductor chip and peripheral member; a second step of attaching a seal tape to between the peripheral member and the die assembly such that the seal tape adheres to part of a surface of the peripheral member; a third step of encapsulating the semiconductor chip and the peripheral member, except for at least the part of the surface thereof, within a resin encapsulant with the seal tape attached; and a fourth step of removing the seal tape after the third step has been performed. After the fourth step has been performed, at least the part of the surface of the peripheral member is exposed out of the resin encapsulant.

[0032] According to this method, if there is any part to be exposed without fail in the peripheral member, a structure with that part exposed out of the resin encapsulant can be obtained by adhering the seal tape to that part of the peripheral member in the second step. Also, since no resin bur is formed on that part of the peripheral member, either, conventionally required process steps, like water jet, can be eliminated. As a result, the manufacturing process can be simplified, and therefore, the first object is accomplished.

[0033] In the basic method for manufacturing a resin-molded semiconductor device, the first step may include: a first sub-step of preparing, as the peripheral member, a leadframe including inner leads and a region for supporting the semiconductor chip thereon; a sec-

ond sub-step of bonding the semiconductor chip onto the region of the leadframe for supporting the semiconductor chip thereon; and a third sub-step of electrically bonding the semiconductor chip to the inner leads. In the second step, the seal tape may be adhered to the back surfaces of the inner leads.

[0034] According to this method, a resin-molded semiconductor device, in which a semiconductor chip, connected to a lead-frame, is provided within a resin encapsulant, is obtained. Also, the back surfaces of the inner leads never fail to be exposed out of the resin encapsulant. Furthermore, by regulating the pressure of the inner leads against the seal tape, the protrusion height of the inner leads as measured from the back surface of the resin encapsulant, i.e., the standoff height of the inner leads, can be adjusted. Accordingly, a resin-molded semiconductor device, attaining the effects of the first resin-molded semiconductor device described above, can be formed easily.

[0035] In the method for manufacturing a resin-molded semiconductor device including the leadframe, in the first sub-step of the first step, a die pad may be formed as the region for supporting the semiconductor chip thereon. Support leads may be formed for supporting the die pad. And a depressed portion for elevating the die pad above the inner leads may be formed in each said support lead. In the second sub-step of the first step, the semiconductor chip may be bonded onto the die pad. In the third sub-step of the first step, the semiconductor chip, which has been bonded onto the die pad, may be electrically bonded to the inner leads via metal fine wires. And in the second step, the seal tape may be adhered only to the back surfaces of the inner leads in the leadframe.

[0036] According to this method, the resin encapsulant can exist under the back of the die pad without increasing the total thickness of the resin-molded semiconductor device so much. As a result, the force of the resin encapsulant holding the die pad can be increased and a thinner resin-molded semiconductor device can be formed easily.

[0037] The method for manufacturing a resin-molded semiconductor device including the leadframe may further include the step of cutting off part of each said inner lead laterally protruding out of the resin encapsulant such that end faces of the inner leads are substantially flush with the side faces of the resin encapsulant after the fourth step has been performed.

[0038] According to this method, a laterally protruding portion can be eliminated from each inner lead. As a result, a resin-molded semiconductor device with a reduced area can also be formed.

[0039] In the method for manufacturing a resin-molded semiconductor device including the leadframe, in the first sub-step of the first step, the leadframe prepared may have been plated with nickel (Ni), palladium (Pd) and gold (Au) layers.

[0040] According to this method, plated layers of qual-

ity can be formed by pre-plating, and the use of a seal tape can eliminate additional process steps for removing resin bur, such as a water jet process step, which are usually performed after resin encapsulation. Accordingly, even when resin bur should be removed, the plated layers do not peel off.

[0041] In the method for manufacturing a resin-molded semiconductor device including the leadframe, in the second step, the seal tape attached may have such a thickness as corresponding to a predetermined value, which is equal to the height of the lower surfaces of the inner leads protruding downward from the back surface of the resin encapsulant after the resin encapsulation.

[0042] According to this method, the protrusion height of the inner leads can be easily adjusted based on the thickness of the seal tape. Accordingly, not only the force of the resin encapsulant holding the inner leads, but also the standoff height provided for making the lower part of each inner lead function as an external terminal can be controlled at respect

[0043] tively adequate values. In the basic method for manufacturing a resin-molded semiconductor device, the first step may include: a first sub-step of preparing a substrate as the peripheral member, the upper surface of the substrate being provided with interconnects, the back surface of the substrate being provided with external electrodes to be connected to the interconnects; a second sub-step of bonding the semiconductor chip onto the upper surface of the substrate; and a third sub-step of electrically connecting the semiconductor chip to the interconnects on the upper surface of the substrate via connection members. In the second step, the seal tape may be adhered at least to the external electrodes.

[0044] According to this method, a resin-molded semiconductor device of a substrate-bonded type, in which external electrodes are exposed out of the resin encapsulant without fail, can be formed.

[0045] In the basic method for manufacturing a resin-molded semiconductor device, the first step may include: a first sub-step of preparing at least a radiator plate as the peripheral member; and a second sub-step of mounting the semiconductor chip on the radiator plate. In the second step, the seal tape may be attached to the back surface of the radiator plate.

[0046] According to this method, a resin-molded semiconductor device including a radiator plate with good radiation properties, in which no resin encapsulant overflows to reach the back of the radiator plate, can be formed.

[0047] In the method for manufacturing a resin-molded semiconductor device including the radiator plate, in the first sub-step of the first step, a leadframe including leads and a bed may be further prepared as the peripheral member. In the second sub-step of the first step, the semiconductor chip may be bonded onto the bed and then the bed may be mounted onto the radiator plate, thereby mounting the semiconductor chip

over the radiator plate.

[0048] According to this method, a resin-molded semiconductor device including a radiator plate can be formed easily by using a leadframe.

[0049] In the basic method for manufacturing a resin-molded semiconductor device, in the first step, a lead assembly, including inner and outer leads, may be prepared as the peripheral member. In the second step, the seal tape may be adhered to between the inner leads and the molding die assembly so as to be attached to part of the surface of each said inner lead. In the third step, all the members, except for at least the part of the surface of each said inner lead, may be encapsulated within the resin encapsulant with the seal tape attached, thereby forming a resin package including an opening and a recess within the opening. The method may further include, posterior to the fourth step, the steps of: mounting the semiconductor chip having the electrode pads into the recess of the resin package; electrically connecting the electrode pads of the semiconductor chip to the inner leads via connection members; and sealing the opening with a sealing member. After the fourth step has been performed, at least the part of the surface of each said inner lead may be exposed out of the resin encapsulant.

[0050] According to this method, it is possible to form easily a resin-molded semiconductor device, which a solid-state imaging device or the like, requiring an overlying free space, is built in. In such a case, a connection portion between an inner lead and the semiconductor chip can be exposed out of the resin encapsulant without fail.

BRIEF DESCRIPTION OF DRAWINGS

[0051]

Figures 1(a) and 1(b) are respectively plan view and cross-sectional view of a resin-molded semiconductor device according to a first embodiment of the present invention, in which a resin encapsulant is illustrated as being transparent.

Figure 2 is a cross-sectional view illustrating the process step of preparing a leadframe during a manufacturing process of the resin-molded semiconductor device in the first embodiment.

Figure 3 is a cross-sectional view illustrating the process step of bonding a semiconductor chip onto a die pad during the manufacturing process of the resin-molded semiconductor device in the first embodiment.

Figure 4 is a cross-sectional view illustrating the process step of forming metal fine wires during the manufacturing process of the resin-molded semiconductor device in the first embodiment.

Figure 5 is a cross-sectional view illustrating the process step of placing a seal tape under the leadframe during the manufacturing process of the

resin-molded semiconductor device in the first embodiment.

Figure 6 is a cross-sectional view illustrating a resin encapsulation process step during the manufacturing process of the resin-molded semiconductor device in the first embodiment. 5

Figure 7 is a cross-sectional view of the resin-molded semiconductor device after the process step of cutting off the ends of the inner leads is finished during the manufacturing process of the resin-molded semiconductor device in the first embodiment. 10

Figure 8 is a partial bottom view of the resin-molded semiconductor device formed by the manufacturing process of the resin-molded semiconductor device in the first embodiment. 15

Figure 9 is a cross-sectional view of a resin-molded semiconductor device of a substrate-bonded type according to a second embodiment of the present invention. 20

Figures 10(a) and 10(b) are cross-sectional views illustrating the process step of bonding a semiconductor chip onto the substrate with metal fine wires and the process step of mounting a semiconductor chip onto the substrate with bumps, respectively, during a manufacturing process of the resin-molded semiconductor device in the second embodiment. 25

Figure 11 is a cross-sectional view illustrating a resin encapsulation process step during the manufacturing process of the resin-molded semiconductor device in the second embodiment. 30

Figure 12 is a cross-sectional view of a resin-molded assembly after the seal tape has been removed during the manufacturing process of the resin-molded semiconductor device in the second embodiment. 35

Figure 13 is a cross-sectional view of a resin-molded semiconductor device including a radiator plate according to a third embodiment of the present invention. 40

Figure 14 is a cross-sectional view illustrating the process step of preparing a leadframe during a manufacturing process of the resin-molded semiconductor device in the third embodiment. 45

Figure 15 is a cross-sectional view illustrating the process step of bonding a semiconductor chip onto a radiator plate and forming metal fine wires during the manufacturing process of the resin-molded semiconductor device in the third embodiment. 50

Figure 16 is a cross-sectional view illustrating the process step of placing a seal tape under the radiator plate and the leadframe during the manufacturing process of the resin-molded semiconductor device in the third embodiment. 55

Figure 17 is a cross-sectional view illustrating a resin encapsulation process step during the manufacturing process of the resin-molded semiconductor device in the third embodiment.

Figure 18 is a cross-sectional view of the resin-molded semiconductor device after the seal tape has been removed during the manufacturing process of the resin-molded semiconductor device in the third embodiment.

Figure 19 is a cross-sectional view of a resin-molded semiconductor device as a CCD package according to a fourth embodiment of the present invention.

Figure 20 is a cross-sectional view illustrating a resin encapsulation process step during a manufacturing process of the resin-molded semiconductor device in the fourth embodiment.

Figure 21 is a cross-sectional view illustrating the process step of removing a seal tape after the resin encapsulation during the manufacturing process of the resin-molded semiconductor device in the fourth embodiment.

Figure 22 is a cross-sectional view illustrating the process step of forming metal fine wires and sealing with seal glass during the manufacturing process of the resin-molded semiconductor device in the fourth embodiment.

Figures 23(a) and 23(b) are respectively plan view and cross-sectional view of a conventional resin-molded semiconductor device of the type including external electrodes on its back.

Figure 24 is a cross-sectional view of a conventional resin-molded semiconductor device ensuring a standoff height by providing ball electrodes for the external electrodes.

Figure 25 is a cross-sectional view illustrating the process step of preparing a leadframe during a conventional manufacturing process of the resin-molded semiconductor device.

Figure 26 is a cross-sectional view illustrating the process step of bonding a semiconductor chip onto a die pad during the conventional manufacturing process of the resin-molded semiconductor device.

Figure 27 is a cross-sectional view illustrating the process step of forming metal fine wires during the conventional manufacturing process of the resin-molded semiconductor device.

Figure 28 is a cross-sectional view illustrating a resin encapsulation process step during the conventional manufacturing process of the resin-molded semiconductor device.

Figure 29 is a cross-sectional view of the resin-molded semiconductor device after the resin encapsulation during the conventional manufacturing process of the resin-molded semiconductor device.

Figure 30 is a bottom view of the resin-molded semiconductor device formed by the conventional manufacturing process of the resin-molded semiconductor device.

BEST MODE FOR CARRYING OUT THE INVENTION

EMBODIMENT 1

[0052] Figure 1(a) is a plan view of a resin-molded semiconductor device according to a first embodiment, and Figure 1(b) is a cross-sectional view thereof taken along the line 1b-1b in Figure 1(a). In Figure 1(a), a resin encapsulant 17 is illustrated as being transparent, a semiconductor chip 15 has a contour as indicated by the dashed line, and the illustration of metal fine wires 16 is omitted.

[0053] As shown in Figures 1(a) and 1(b), the resin-molded semiconductor device of this embodiment includes a leadframe consisting of: inner leads 12; a die pad 13 for supporting the semiconductor chip thereon; and support leads 14 for supporting the die pad 13. The semiconductor chip 15 is bonded on the die pad 13 with an adhesive, and electrode pads (not shown) of the semiconductor chip 15 are electrically connected to the inner leads 12 with metal fine wires 16. And the inner leads 12, die pad 13, support leads 14, semiconductor chip 15 and metal fine wires 16 are encapsulated within the resin encapsulant 17. Also, the die pad 13 is elevated by depressed portions 19 of the support leads 14 so as to be located above the inner leads 12. Accordingly, after the chip, frame and so on have been molded with the resin encapsulant 17, a thin layer of the resin encapsulant 17 exists under the back surface of the die pad 13.

[0054] Hereinafter, the features of the resin-molded semiconductor device according to this embodiment will be described. No resin encapsulant 17 exists on the respective lower parts of the inner leads 12. In other words, the respective lower surfaces of the inner leads 12 are exposed, and are used as interconnection with a motherboard. That is to say, the respective lower parts of the inner leads 12 function as external electrodes 18. In addition, virtually no resin burr, which ordinarily sticks out during a resin encapsulation process step, exists on the external electrodes 18. And the external electrodes 18 slightly protrude downward from the back surface of the resin encapsulant 17. The external electrodes 18 can be easily formed in such a shape by the manufacturing process described later so as to protrude downward and have no resin burr thereon.

[0055] In the resin-molded semiconductor device of this embodiment, no outer leads, which function as external electrode terminals in many conventional structures, exist beside the inner leads 12. Instead, the lower part of each inner lead 12, including the lower and side faces thereof, functions as an external electrode 18. Accordingly, such a structure contributes to downsizing of a semiconductor device. Moreover, since no resin burr exists on the respective lower surfaces of the inner leads 12, i.e., the lower surfaces of the external electrodes 18, the electrodes of the motherboard can be bonded to these external electrodes 18 with more reliability.

Furthermore, the external electrodes 18 are formed to protrude from the plane of the resin encapsulant 17. Thus, a standoff height, which should be secured in bonding the external electrodes to the electrodes of the motherboard during mounting of the resin-molded semiconductor device onto the motherboard, has already been provided for the external electrodes 18. Accordingly, the external electrodes 18 can be used as external terminals as they are. Also, unlike the conventional process, there is no need to attach solder balls to the external electrodes 18 during mounting of the device onto the motherboard. Therefore, this method is advantageous in the number and cost of manufacturing process steps.

[0056] In addition, the die pad 13 is elevated above the inner leads 12 and a thin layer of the resin encapsulant 17 exists on the back of the die pad 13. As a result, the reliability of the resin-molded semiconductor device improves.

[0057] In this embodiment, the die pad 13 is provided for supporting the semiconductor chip 15 thereon. Alternatively, even if it were not for the die pad 13, the semiconductor chip still could be supported by the respective insulated ends of the inner leads or mounted on a plastic tape. That is to say, the die pad 13 is not always required, and this embodiment is applicable to a leadframe without a die pad.

[0058] Also, in this embodiment, the metal fine wires 16 are used as means for electrically connecting the electrodes of the semiconductor chip 15 to the inner leads 12. Alternatively, the electrodes of the semiconductor chip 15 may be electrically connected to the inner leads 12 by flip-chip bonding (i.e., with bumps interposed therebetween) or direct bonding (i.e., by forming a eutectic alloy).

[0059] Next, a method for manufacturing the resin-molded semiconductor device of this embodiment will be described with reference to the drawings. Figures 2 through 7 are cross-sectional views illustrating a manufacturing process of the resin-molded semiconductor device of this embodiment.

[0060] First, in the process step shown in Figure 2, a lead-frame 20, including inner leads 12 and a die pad 13 for supporting a semiconductor chip thereon, is prepared. Although the die pad 13 is actually supported by support leads, the support leads are not illustrated in Figure 2 because the leads are not included in this cross section. Also, a depressed portion is formed in each of these support leads, thereby the die pad 13 is elevated above the plane on which the inner leads 12 are located. The leadframe 20 prepared is not provided with tie bars used for stopping the outflow of a resin encapsulant during resin encapsulation.

[0061] The leadframe 20 of this embodiment is formed by plating a frame made of copper (Cu) with the three metal layers of: an undercoat nickel (Ni) layer; a palladium (Pd) layer plated thereon; and an outermost thin gold (Au) layer. Alternatively, the leadframe 20 may be

made of any raw material other than copper (Cu), e.g., Alloy 42. Also, the leadframe 20 may be plated with any noble metals other than nickel (Ni), palladium (Pd) and gold (Au). Furthermore, the number of plated layers does not have to be three.

[0062] Next, in the process step shown in Figure 3, a semiconductor chip 15 is mounted and bonded, with an adhesive, onto the die pad of the leadframe prepared. This process step is so-called "die bonding". It should be noted that any support member other than a leadframe may be used to support the semiconductor chip. For example, a TAB tape or a substrate may also be used.

[0063] Then, in the process step shown in Figure 4, the semiconductor chip 15, which has been bonded onto the die pad 13, is electrically bonded to the inner leads 12 with metal fine wires 16. This process step is so-called "wire bonding". The metal fine wires may be made of an appropriately selected material such as aluminum (Al) or gold (Au). Optionally, the semiconductor chip 15 may be electrically connected to the inner leads 12 via bumps or the like, not the metal fine wires 16.

[0064] Subsequently, in the process step shown in Figure 5, a seal tape 21 is attached to the respective back surfaces of the inner leads 12 with the semiconductor chip 15 bonded onto the die pad 13 of the leadframe.

[0065] The seal tape 21 is used as a sort of mask for preventing the resin encapsulant from overflowing and reaching the respective lower surfaces of the inner leads 12 during resin encapsulation. The existence of the seal tape 21 can prevent resin burr from being formed on the back surfaces of the inner leads 12. The seal tape 21 attached to the inner leads 12 and so on may be any resin-based tape, which is mainly composed of polyethylene terephthalate, polyimide, polycarbonate or the like, can be easily peeled after the resin encapsulation and has some resistance to an elevated-temperature environment during the resin encapsulation. In this embodiment, a tape mainly composed of polyethylene terephthalate is used and the thickness thereof is 50 μm .

[0066] In this embodiment, the seal tape 21 is attached to the entire back surface of the leadframe, but is adhered only to the surfaces of the inner leads 12 of the leadframe. That is to say, the seal tape 21 does not adhere to the back surface of the die pad 13, which is elevated by the depressed portions of the support leads. Alternatively, the radiation properties of the die pad 13 may be increased by adhering the seal tape 21 to the back surface of the die pad 13 and then peeling the seal tape 21 off to expose the back surface of the die pad 13 after the resin encapsulation step.

[0067] Then, in the process step shown in Figure 6, the leadframe, on which the semiconductor chip 15 has been bonded and to which the seal tape 21 has been attached, is introduced into a die assembly. And a resin encapsulant 17 is poured into the die assembly to mold

the chip, frame and so on with the encapsulant 17. In this case, resin encapsulation is performed while pressing downward the ends 22 of the inner leads 12 of the leadframe with the dies such that the resin encapsulant 17 does not reach the respective lower surfaces of the inner leads 12. The resin encapsulation is also performed with the seal tape 21 on the back of the inner leads 12 pressed against the face of the die.

[0068] Finally, in the process step shown in Figure 7, the seal tape 21, which has been attached to the respective back surfaces of the inner leads 12, is peeled off and removed, thereby forming external electrodes 18, protruding from the back surface of the resin encapsulant 17. Then, the ends of the inner leads 12 are cut off to be substantially flush with the side faces of the resin encapsulant 17, thereby completing a resin-molded semiconductor device such as that shown in Figure 7.

[0069] Figure 8 is a partial bottom view of the resin-molded semiconductor device of this embodiment, illustrating respective parts of the external electrodes 18 on a larger scale. As shown in Figure 8, in this embodiment, the formation of resin burr on the back and side faces of the inner leads 12, i.e., on the surfaces of the external electrodes 18, can be prevented. This is because the resin encapsulation process step is performed with the seal tape 21 adhered to the back surface of the leadframe. Also, unlike a conventional manufacturing process, it is possible to prevent the resin encapsulant 17 from reaching the surfaces of the external electrodes 18 and part of the external electrodes 18 from being buried in the resin encapsulant 17.

[0070] According to the manufacturing method of this embodiment, the seal tape 21 is attached in advance to the respective back surfaces of the inner leads 12 before the resin encapsulation process step. Thus, the resin encapsulant 17 cannot reach, and no resin burr is formed on, the back surfaces of the inner leads 12 functioning as external electrodes. Accordingly, resin burr, formed on the inner leads, need not be removed therefrom using water jet or the like, unlike a conventional method for manufacturing a resin-molded semiconductor device with the lower surfaces of inner leads entirely exposed. That is to say, since this troublesome step of deburring can be omitted, this process is simple enough to mass-produce a great number of resin-molded semiconductor devices. In addition, peeling of metal plated layers such as nickel (Ni), palladium (Pd) and gold (Au) on the leadframe, which might happen during the conventional deburring process step using water jet, for example, can be eliminated. For that reason, the leadframe can be plated in advance with these metal layers before the resin encapsulation process step.

[0071] In addition, since the external electrodes 18 formed by the manufacturing process of this embodiment protrude from the resin encapsulant 17, the external electrodes 18 can be used as external terminals as they are, without providing solder balls as in a conven-

tional process.

[0072] Although the step of deburring using water jet can be omitted, the step of attaching the seal tape should be additionally performed in this embodiment. However, the step of attaching the seal tape 21 is more cost-effective than the water jet process step. And it is easier to control the former process step than the latter. Accordingly, the process can be simplified without fail. Among other things, the method of this embodiment is particularly advantageous in that attaching the seal tape can eliminate the water jet process step conventionally required, which has brought about various quality-control problems like peeling of metal plated layers from the leadframe and deposition of impurities thereon. Thus, in this embodiment, the plated metal layers are much less likely to peel off. Also, it is true that resin burr still may be formed in this embodiment depending on the attachment state of the seal tape. Even so, the resulting resin burr is very thin, and can be easily removed with water jet at a low water pressure. Accordingly, should such a water jet process step be required, peeling of the metal plated layers still can be prevented. And there is no problem if the leadframe is plated with these metal layers beforehand.

[0073] It should be noted that a level difference is formed between the respective back surfaces of the inner leads 12 and that of the resin encapsulant 17 as shown in Figure 6. This is because the seal tape 21 softens and thermally shrinks owing to the heat applied by the molten resin encapsulant during the resin encapsulation step, and the inner leads 12 are strongly forced into the seal tape 21. Accordingly, in this structure, the back surfaces of the inner leads 12 protrude from that of the resin encapsulant 17. As a result, a standoff height of the external electrodes 18, or the respective lower parts of the inner leads 12, can be secured. Therefore, these protruding external electrodes 18 can be used as external terminals as they are.

[0074] The height of the level difference between the respective back surfaces of the inner leads 12 and that of the resin encapsulant 17 can be controlled based on the thickness of the seal tape 21 attached before the step of encapsulating. For example, in this embodiment, since the thickness of the seal tape 21 is 50 μm , the height of the level difference, i.e., the protrusion height of the external electrodes 18, is usually about one-half of the thickness, and 50 μm at its maximum. That is to say, the height of a portion of the seal tape 21 upwardly forced as measured from the back surfaces of the inner leads 12 is determined depending on the thickness of the seal tape 21. In other words, the protrusion height of the external electrodes 18 can be self-controlled by the thickness of the seal tape 21, thus facilitating the manufacturing. The protrusion height of the external electrodes 18 can be controlled only by adjusting the thickness of the seal tape 21 during a mass production process, and there is no need to provide an additional process step separately. Accordingly, the manufacturing

method of this embodiment is extremely advantageous in terms of the process control cost. It should be noted that as for the seal tape 21 to be attached, the hardness of a material used, the thickness and the thermal softening properties thereof can be determined depending on the desired height of the level difference.

[0075] In the resin-molded semiconductor device of this embodiment, although the resin encapsulant 17 exists on the back of the die pad 13 as shown in Figure 2, the thickness thereof is equal to the elevated height of the die pad 13, and is extremely small. Thus, the resin-molded semiconductor device of this embodiment is substantially one-side-encapsulated semiconductor device.

[0076] In the foregoing exemplary embodiment, the seal tape 21 is attached in advance to the respective lower surfaces of the inner leads 12 of the leadframe before the resin encapsulation process step. Instead of attaching the tape to the leadframe this way, the seal tape 21 may be placed on a molding die assembly and the leadframe may be adhered thereto. In such a case, the seal tape can be reeled off and supplied to the molding die assembly as will be described later. As a result, the process can be further simplified.

[0077] Also, in this embodiment, a manufacturing process, in which resin encapsulation is performed with the seal tape attached to the back of the leadframe, has been exemplified. However, the method of the present invention is not limited to a semiconductor device including a leadframe. A technique of using a seal tape during a resin encapsulation process step, which is a basic concept of the present invention, is broadly applicable to any resin encapsulation process step for a semiconductor device incorporating a semiconductor chip and including some members to be molded with resin. Thus, this technique is applicable to a resin encapsulation process step for a semiconductor device of a TAB or substrate type.

EMBODIMENT 2

[0078] Next, a second embodiment of the present invention will be described. Figure 9 is a cross-sectional view illustrating a resin-molded semiconductor device of a substrate-bonded type according to this embodiment.

[0079] As shown in Figure 9, the resin-molded semiconductor device of this embodiment is of a substrate-bonded type such as a BGA (ball grid array) type. The device includes: a substrate 24 made of single- or multiple-layered glass epoxy plastic or ceramic; a semiconductor chip 25 mounted on the substrate 24; and metal fine wires 26 for electrically connecting interconnects (not shown) formed on the upper surface of the substrate 24 to electrode pads (not shown) of the semiconductor chip 25. And over the upper surface of the substrate 24, the semiconductor chip 25, interconnects and metal fine wires 26 are molded with an insulating resin encapsulant 27. On the back of the substrate 24,

external electrode pads (lands) 28 are formed. The interconnects on the upper surface of the substrate 24 are connected to the external electrode pads (lands) 28 on the back surface of the substrate 24 by way of through holes or via holes.

[0080] In this embodiment, ball electrodes 29, which are made of a conductive material for bonding the substrate 24 to an external board, are provided for the external electrode pads 28. However, the ball electrodes 29 do not have to be provided. Also, the substrate 24 may be a thin polyimide film, for example.

[0081] According to this embodiment, the assembly is transfer-molded with a resin encapsulant while a seal tape is attached to the back of the substrate 24 during a resin encapsulation process step as will be described later. Thus, it is possible to prevent the resin encapsulant 27 from overflowing to reach the external electrode pads 28. Consequently, a surface to be connected to a motherboard can be free from resin bur, which would otherwise be formed on the external electrode pads 28, and the reliability in connecting with the ball electrodes 29 interposed can be improved.

[0082] Next, a method for manufacturing the resin-molded semiconductor device of this embodiment will be described with reference to the drawings. Figures 10 through 12 are cross-sectional views illustrating, on a step-by-step basis, a manufacturing process for the BGA-type resin-molded semiconductor device of this embodiment.

[0083] First, in the process step shown in Figure 10(a), interconnects (not shown) are formed on the substrate 24, which is a single- or multiple-layered glass epoxy plastic or ceramic plate. Through holes or via holes are formed in the substrate 24. And the external electrode pads 28 are formed on the back of the substrate 24. Thereafter, the semiconductor chip 25 is bonded at a predetermined position on the substrate 24 with a die-bonding member, for example, and the interconnects on the substrate are connected to electrode pads (not shown) on the semiconductor chip with the metal fine wires 26.

[0084] Alternatively, the semiconductor chip 25 may be mounted onto the substrate 24 in a facedown manner shown in Figure 10(b). In such a case, the interconnects on the substrate 24 are ordinarily bonded to the electrode pads on the semiconductor chip 25 with metal balls 30 like bumps. As the case may be, the interconnects on the substrate 24 and the electrode pads on the semiconductor chip 25 are alloyed and directly bonded to each other. The subsequent process steps will be described on the supposition that the bonding structure shown in Figure 10(a) has been adopted here.

[0085] Next, in the process step shown in Figure 11, resin encapsulation is performed using a molding die assembly 31, consisting of lower and upper dies 31a and 31b, to mold the semiconductor chip 25, interconnects, and metal fine wires 26 over the substrate 24. In this step, before the resin encapsulation is performed, a

first seal tape 32a is attached to the back of the substrate 24, i.e., to the upper surface of the lower die 31a of the molding die assembly 31, thereby adhering the seal tape 32a to the lower surfaces of the external electrode pads 28 of the substrate 24. In this case, the pressure applied to the die assembly forces the external electrode pads 28 into the seal tape 32a. As a result, the seal tape 32a adheres to the back of the substrate 24 and to lower surfaces of the external electrodes 28. In addition, a second seal tape 32b is also adhered to the lower surface of the upper die 31b of the molding die assembly 31. By transfer-molding the assembly with the resin encapsulant 27 in such a state, only the regions surrounding the semiconductor chip 25 can be molded with the resin over the upper surface of the substrate 24 and the overflow of the resin encapsulant to the back of the substrate 24 can be prevented. And as described above, it is possible to prevent the resin bur from being formed on the external electrode pads 28 on the back of the substrate 24.

[0086] Also, since not only the first seal tape 31a but also the second seal tape 32b are used, the resin encapsulant 27 can be advantageously released from the upper die 31b easily.

[0087] According to such a resin encapsulation technique, resin encapsulation is performed with pressure applied to the substrate 24 through the molding die assembly 31. Since pressure is herein applied to the structure with the substrate 24 interposed between the first and second seal tapes 32a and 32b, the force applied to the substrate 24 can be cushioned and the fracture or deformation of the substrate 24 can be advantageously prevented during the resin encapsulation.

[0088] Finally, in the process step shown in Figure 12, the resin-molded assembly, in which the regions surrounding the semiconductor chip 25 over the substrate 24 are molded with the resin encapsulant 27, is released from the molding die assembly 31. As a result, a resin-molded package, in which no resin encapsulant has reached the external electrode pads 28 on the back of the substrate 24, is obtained.

[0089] If the ball electrodes 29 (indicated by the phantom lines) are provided for the external electrode pads 28 on the back of the substrate 24, a resin-molded semiconductor device of a BGA type can be obtained. Alternatively, if these external electrode pads 28 have been formed with a relatively large thickness, then the external electrode pads 28 may be used as external terminals as they are without forming the ball electrodes 29 thereon.

[0090] As can be understood, in the method for manufacturing a BGA-type resin-molded semiconductor device according to this embodiment, the first and second seal tapes 32a and 32b are used. By utilizing the elasticity thereof, deformation of the substrate 24 within the molding die assembly can be suppressed, and deposition of the resin encapsulant or foreign particles on

the external electrode pads 28 of the substrate 24 can be prevented.

[0091] Of the first and second seal tapes 32a and 32b, the first seal tape 32a is not always required. Even if only the second seal tape 32b is provided, it is also possible to prevent the overflow of the resin encapsulant to the sides or back of the substrate 24, since the second seal tape 32b is in contact with the upper surface of the substrate 24.

[0092] Furthermore, the seal tape 32a does not have to be adhered to the entire back face of the substrate 24. The seal tape 32a is only required to adhere to at least the lower surfaces of the external electrode pads 28.

EMBODIMENT 3

[0093] Next, a third embodiment of the present invention will be described. Figure 13 is a cross-sectional view illustrating a resin-molded semiconductor device according to this embodiment. The resin-molded semiconductor device of this embodiment includes: a radiator plate; and a semiconductor chip incorporating a device generating a relatively large quantity of heat, e.g., a high-power transistor.

[0094] As shown in Figure 13, the semiconductor device of this embodiment includes: a bed 33, or a support for a leadframe; a semiconductor chip 34 bonded on the bed 33 with a die-bonding member; a metal terminal 35 of the leadframe; a metal fine wire 36 for electrically connecting the metal terminal 35 to the semiconductor chip 34; and a radiator plate 37 for supporting the bed 33 thereon. In this structure, all the members are entirely molded with an insulating resin encapsulant 38, except for the bottom of the radiator plate 37 and part of the metal terminal 35 protruding out of the resin encapsulant 38 as an external terminal. That is to say, the upper and side faces of the radiator plate 37, bed 33, semiconductor chip 34, metal fine wire 36 and the other part of the metal terminal 35 are molded with the resin encapsulant 38.

[0095] According to this embodiment, the assembly is transfer-molded with a seal tape attached to the back of the radiator plate 37 during a resin encapsulation process step as will be described later. Thus, it is possible to prevent the resin encapsulant 38 from overflowing to reach the back of the radiator plate 37 and forming resin bur thereon. Accordingly, the radiating face (back surface) of the radiator plate 37 can maintain its function. That is to say, its function of dissipating the heat, which has been generated from the semiconductor chip of the semiconductor device, to the outside can be maintained and improved.

[0096] Next, a method for manufacturing the resin-molded semiconductor device of this embodiment will be described with reference to the drawings. Figures 14 through 18 are cross-sectional views illustrating, on a step-by-step basis, a manufacturing process for the

resin-molded semiconductor device including a radiator plate according to this embodiment.

[0097] First, in the process step shown in Figure 14, a lead-frame, including the bed 33, or a support for a semiconductor chip, and the metal terminal 35, is prepared. The semiconductor chip 34 is bonded onto the upper surface of the bed 33 with a die-bonding member. Then, the semiconductor chip 34 is connected to the metal terminal 36 with the metal fine wire 36.

[0098] Next, in the process step shown in Figure 15, the radiator plate 37 is bonded onto the back of the bed 33. Alternatively, the bed 33 may also be formed with an increased thickness so as to function as a radiator plate by itself.

[0099] Then, in the process step shown in Figure 16, the seal tape 39 is adhered to the back of the radiator plate 37. In this case, the radiator plate 37 with the seal tape 39 adhered thereto may be placed into a molding die assembly. Alternatively, the back of the radiator plate 37 may be adhered to the seal tape 39 by attaching in advance the seal tape 39 to the molding die assembly, more specifically onto the lower die, and then mounting the radiator plate 37 onto the lower die.

[0100] Subsequently, in the process step shown in Figure 17, the bed 33, semiconductor chip 34, metal fine wire 36 and part of the metal terminal 35 are molded with the insulating resin encapsulant 38 while the seal tape 39 is adhered to the back of the radiator plate 37. In this case, the bottom of the radiator plate 37 and the other part of the metal terminal 35 are exposed out of the resin encapsulant 38.

[0101] Finally, in the process step shown in Figure 18, the seal tape 39 is peeled off from the back of the radiator plate 37 and the metal terminal 35 is folded, thereby completing a resin-molded semiconductor device shown in Figure 18, in which the back of the radiator plate 37 is exposed.

[0102] In the method for manufacturing the resin-molded semiconductor device including a radiator plate according to this embodiment, the seal tape 39, which is adhered to the back of the radiator plate 37, is used during the resin encapsulation process step, thereby preventing the overflow of the resin encapsulant onto the back of the radiator plate 37 and the formation of resin bur thereon. In other words, since the back of the radiator plate 37 can be exposed without fail, a resin-molded semiconductor device can be obtained without lessening the radiation effect of the radiator plate 37. Also, since the resin encapsulation is performed with the seal tape 39 adhered to the back of the radiator plate 37, part of the seal tape 39 is forced inward to partially cover the sides of the radiator plate 37. As a result, the radiator plate 37 slightly protrudes out of the back of the resin encapsulant after the resin encapsulation is over.

Accordingly, in mounting such a resin-molded semiconductor device onto a motherboard, the entire back surface of the radiator plate 37 can be in contact with the motherboard without fail, thus enhancing the radiation

effect.

EMBODIMENT 4

[0103] Next, a fourth embodiment of the present invention will be described with reference to the drawings. Figure 19 is a cross-sectional view illustrating a resin-molded semiconductor device, like a CCD package, according to this embodiment.

[0104] As shown in Figure 19, the resin-molded semiconductor device of this embodiment includes: a resin package 41 with an opening in the upper part thereof and a recess 42 provided within the opening; a solid-state imaging device 40 bonded onto the bottom of the recess 42 of the resin package 41 with a die-bonding member; inner leads 43 provided near the recess 42 of the resin package 41; outer leads 46, which are connected to the respective inner leads 43 and extend outward through the resin package 41; and metal fine wires 44 for electrically connecting electrode pads (not shown) on the solid-state imaging device 40 to the inner leads 43 on the resin package 41. Also, the opening of the resin package 41 is sealed with sealing glass 45. The outer leads 46, protruding out of the resin package 41, are folded downward. It should be noted that the resin package 41 is a package that has been integrally transfer-molded with an insulating resin.

[0105] In the resin-molded semiconductor device according to this embodiment, the resin package 41 is formed by performing transfer-molding with a seal tape attached onto the inner leads 43 during a resin encapsulation process step as will be described later. Thus, no resin bur is formed on respective upper surfaces of the inner leads 43, but these surfaces are exposed. Accordingly, in this resin-molded semiconductor device, the inner leads 43 can be connected to the solid-state imaging device 40 via the metal fine wires 44 with more reliability.

[0106] Next, a method for manufacturing the resin-molded semiconductor device according to this embodiment, like a CCD package, will be described with reference to the drawings. Figures 20 through 22 are cross-sectional views illustrating, on a step-by-step basis, a manufacturing process for the resin-molded semiconductor device according to this embodiment.

[0107] First, in the process step shown in Figure 20, a lead assembly, including inner and outer leads 43 and 46, is prepared. Before the resin package is molded, the seal tape 47 is attached or adhered to those portions of the lead assembly to be the inner leads 43, thereby preventing the overflow of the resin encapsulant onto the upper surfaces of the inner leads 43. Then, the respective members are transfer-molded with a resin within a molding die assembly consisting of upper and lower dies 51a and 51b, thereby forming the resin package 41. Figure 20 illustrates a state where the resin package 41 has already been formed and the respective surfaces of the inner and outer leads 43 and 46 are cov-

ered with the seal tape 47.

[0108] Then, in the process step shown in Figure 21, the seal tape 47 is peeled off, thereby obtaining a resin package 41, in which the respective upper surfaces of the inner leads 43 are exposed without fail. At an elevated temperature, the seal tape 47 adheres to the inner leads 43 without forming any gap therebetween. Thus, on the exposed surfaces of the inner leads 43, from which the seal tape 47 has been peeled off, no foreign particles, such as resin bur of the resin encapsulant, are deposited.

[0109] Subsequently, in the process step shown in Figure 22, the solid-state imaging device 40 is bonded onto the bottom of the recess 42 provided within the resin package 41. Electrode pads on the solid-state imaging device 40 are connected to the inner leads 43 with the metal fine wires 44. After the opening of the resin package 41 has been sealed with the sealing glass 45, the outer leads 46 are folded. The outer leads 46 may be folded into a desired shape depending on the type of the semiconductor device.

[0110] A resin encapsulation technique using a seal tape according to this embodiment is particularly suitable for manufacturing a semiconductor device including a resin package with an opening in the upper part thereof, e.g., an optical semiconductor device like a CCD or a hologram. In particular, remarkable effects can be attained if this embodiment is applied to molding a resin package including leads.

[0111] Another application of this embodiment will be briefly described. In manufacturing a component, such as an LED, the package of which should have required color or transparency, resin encapsulation can be performed effectively by attaching a seal tape to a molding die assembly in advance such that foreign particles or dirt involved with the molding die assembly are not transferred to the package. As a result, an excellent package can be formed.

INDUSTRIAL APPLICABILITY

[0112] The resin-molded semiconductor device and the method for manufacturing the same according to the present invention are applicable to all sorts of electronic equipment using a semiconductor integrated circuit made up of various types of transistors.

Claims

1. A resin-molded semiconductor device comprising:
 - a semiconductor chip having electrode pads; inner leads;
 - connection members for electrically connecting the electrode pads of the semiconductor chip to the inner leads; and
 - a resin encapsulant for molding the semiconductor chip, the inner leads and the connection

members together,
characterized in that the lower part of each said
inner lead, including at least part of the back
surface thereof, functions as an external elec-
trode, the external electrode protruding down-
ward from the back surface of the resin
encapsulant.

2. The resin-molded semiconductor device of Claim 1,
further comprising:

a die pad for supporting the semiconductor
chip thereon; and
support leads for supporting the die pad,
characterized in that each said support lead
includes a depressed portion for elevating the
die pad above the inner leads.

3. The resin-molded semiconductor device of Claim 1
or 2, characterized in that a protrusion height of the
external electrode as measured from the back sur-
face of the resin encapsulant is in the range from 10
 μm to 40 μm .

4. A method for manufacturing a resin-molded semi-
conductor device, comprising:

a first step of preparing a molding die assem-
bly, a semiconductor chip and a peripheral
member;
a second step of attaching a seal tape to
between the peripheral member and the mold-
ing die assembly such that the seal tape
adheres to part of a surface of the peripheral
member;
a third step of encapsulating the semiconductor
chip and the peripheral member, except for at
least the part of the surface thereof, within a
resin encapsulant with the seal tape attached;
and
a fourth step of removing the seal tape after the
third step has been performed,
characterized in that after the fourth step has
been performed, at least the part of the surface
of the peripheral member is exposed out of the
resin encapsulant.

5. The method for manufacturing a resin-molded semi-
conductor device of Claim 4, characterized in that
the first step comprises:

a first sub-step of preparing, as the peripheral
member, a leadframe including inner leads and
a region for supporting the semiconductor chip
thereon;
a second sub-step of bonding the semiconduc-
tor chip onto the region of the leadframe for
supporting the semiconductor chip thereon;

and

a third sub-step of electrically bonding the semi-
conductor chip to the inner leads, and
that in the second step, the seal tape is
adhered to the back surfaces of the inner leads.

6. The method for manufacturing a resin-molded semi-
conductor device of Claim 5, characterized in that
in the first sub-step of the first step, a die pad is
formed as the region for supporting the semicon-
ductor chip thereon, support leads are formed for
supporting the die pad, and a depressed portion for
elevating the die pad above the inner leads is
formed in each said support lead, and

that in the second sub-step of the first step, the
semiconductor chip is bonded onto the die pad,
and

that in the third sub-step of the first step, the
semiconductor chip, which has been bonded
onto the die pad, is electrically bonded to the
inner leads via metal fine wires, and
that in the second step, the seal tape is
adhered only to the back surfaces of the inner
leads in the leadframe.

7. The method for manufacturing a resin-molded semi-
conductor device of Claim 5 or 6, characterized by
further comprising the step of cutting off part of
each said inner lead laterally protruding out of the
resin encapsulant such that end faces of the inner
leads are substantially flush with the side faces of
the resin encapsulant after the fourth step has been
performed.

8. The method for manufacturing a resin-molded semi-
conductor device of one of Claims 5 to 7, charac-
terized in that in the first sub-step of the first step,
the leadframe prepared has been plated with nickel
(Ni), palladium (Pd) and gold (Au) layers.

9. The method for manufacturing a resin-molded semi-
conductor device of one of Claims 5 to 7, charac-
terized in that in the second step, the seal tape
attached has such a thickness as corresponding to
a predetermined value, which is equal to the height
of the lower surfaces of the inner leads protruding
downward from the back surface of the resin encap-
sulant after the resin encapsulation.

10. The method for manufacturing a resin-molded semi-
conductor device of Claim 4, characterized in that
the first step comprises:

a first sub-step of preparing a substrate as the
peripheral member, the upper surface of the
substrate being provided with interconnects,
the back surface of the substrate being pro-

vided with external electrodes to be connected to the interconnects;

a second sub-step of bonding the semiconductor chip onto the upper surface of the substrate; and

a third sub-step of electrically connecting the semiconductor chip to the interconnects on the upper surface of the substrate via connection members, and

that in the second step, the seal tape is adhered at least to the external electrodes.

11. The method for manufacturing a resin-molded semiconductor device of Claim 4, characterized in that the first step comprises:

a first sub-step of preparing at least a radiator plate as the peripheral member; and

a second sub-step of mounting the semiconductor chip on the radiator plate, and

that in the second step, the seal tape is attached to the back surface of the radiator plate.

12. The method for manufacturing a resin-molded semiconductor device of Claim 4, characterized in that the first step comprises:

a first sub-step of preparing at least a radiator plate as the peripheral member; and

a second sub-step of mounting the semiconductor chip on the radiator plate, and

that in the second step, the seal tape is attached to the back surface of the radiator plate.

13. The method for manufacturing a resin-molded semiconductor device of Claim 12, characterized in that in the first sub-step of the first step, a leadframe including leads and a bed is further prepared as the peripheral member, and

that in the second sub-step of the first step, the semiconductor chip is bonded onto the bed and then the bed is mounted onto the radiator plate, thereby mounting the semiconductor chip over the radiator plate.

14. The method for manufacturing a resin-molded semiconductor device of Claim 4, characterized in that in the first step, a lead assembly, including inner and outer leads, is prepared as the peripheral member, and

that in the second step, the seal tape is adhered to between the inner leads and the molding die assembly so as to be attached to part of the surface of each said inner lead, and

that in the third step, all the members, except for at least the part of the surface of each said inner lead, are encapsulated within the resin encapsulant with the seal tape attached, thereby forming a resin package having an opening and a recess within the opening, and that the method further includes, posterior to the fourth step, the steps of:

mounting the semiconductor chip having the electrode pads into the recess of the resin package;

electrically connecting the electrode pads of the semiconductor chip to the inner leads via connection members; and

sealing the opening with a sealing member, and

that after the fourth step has been performed, at least the part of the surface of each said inner lead is exposed out of the resin encapsulant.

Fig. 1(a)

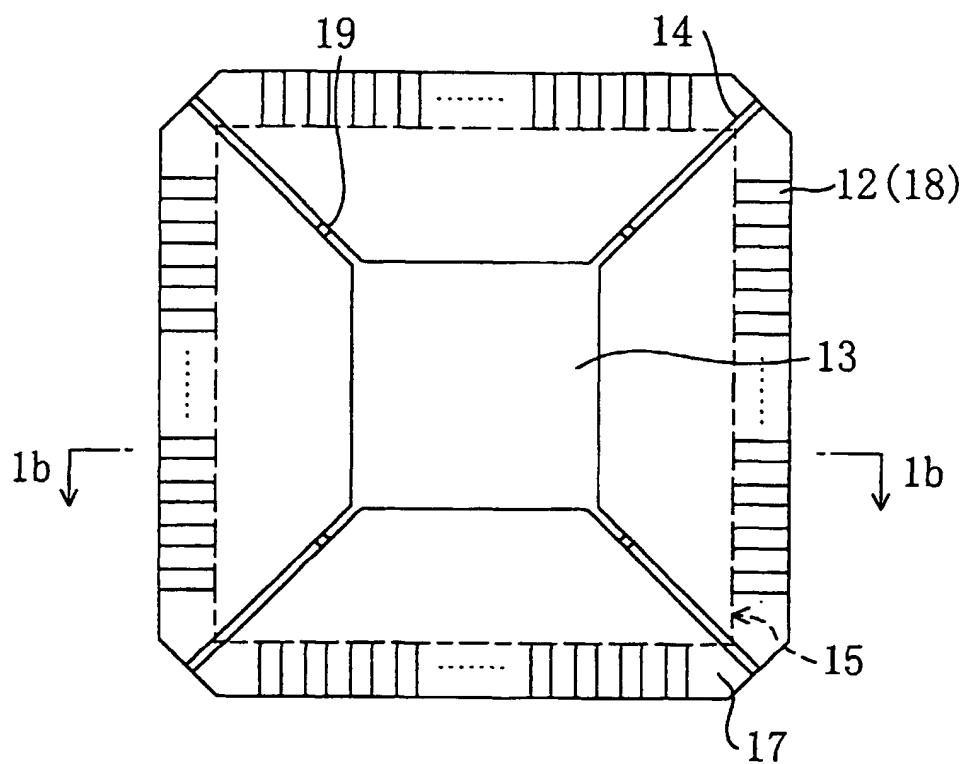


Fig. 1(b)

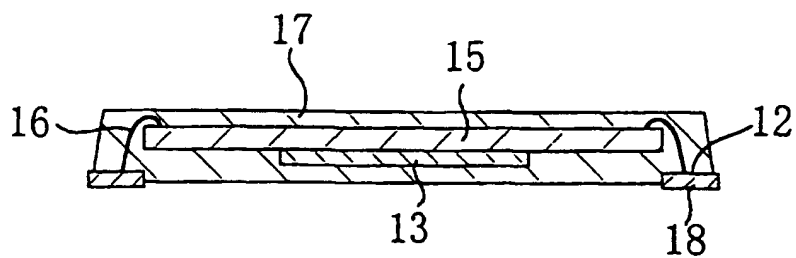


Fig. 2

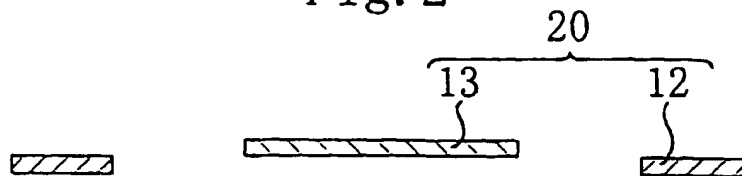


Fig. 3

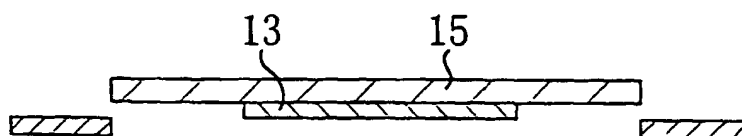


Fig. 4

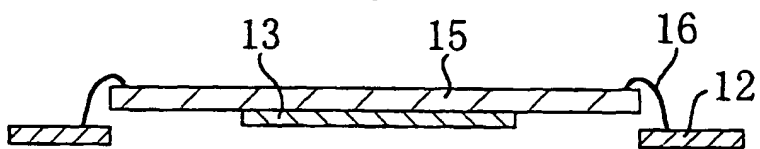


Fig. 5

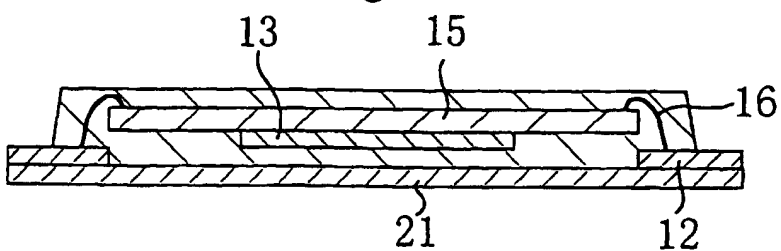


Fig. 6

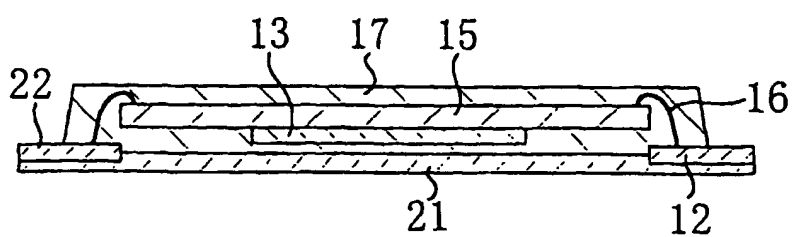


Fig. 7

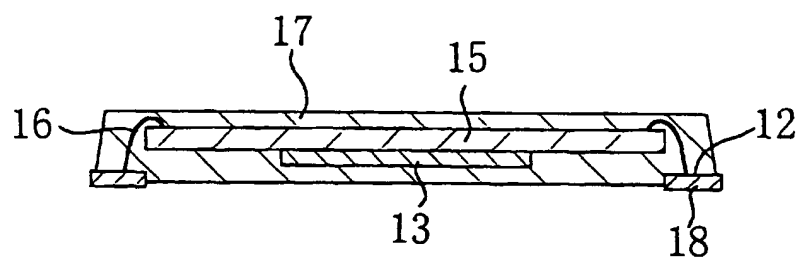


Fig. 8

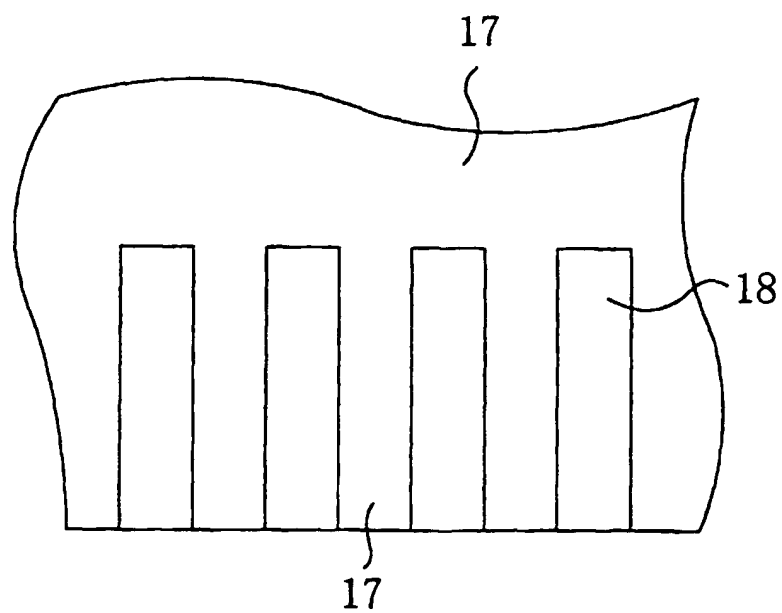


Fig. 9

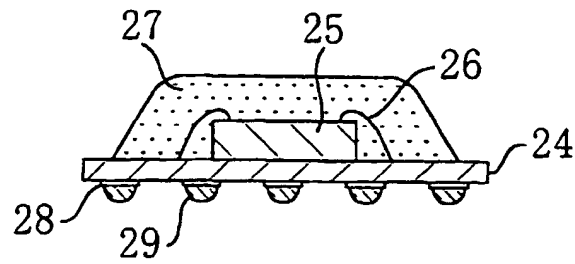


Fig. 10(a)

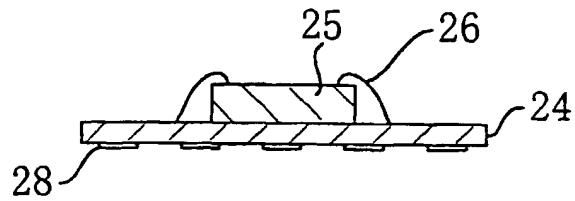


Fig. 10(b)

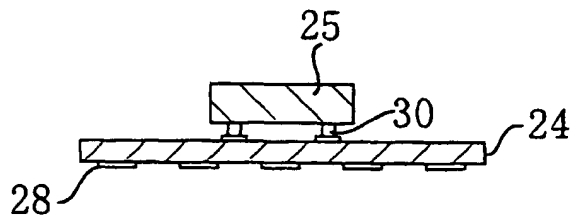


Fig. 11

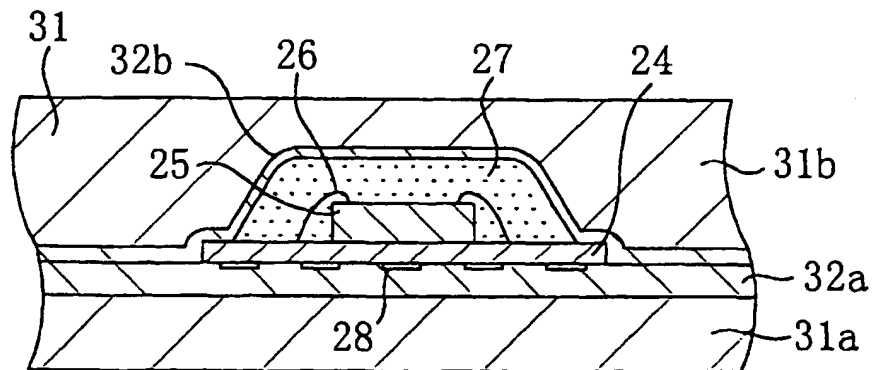
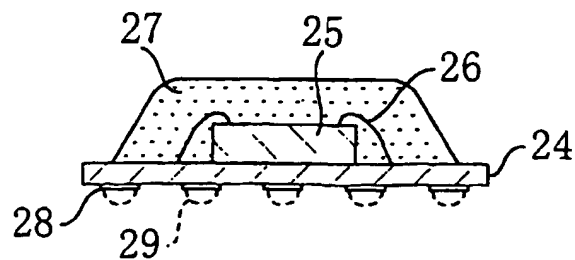
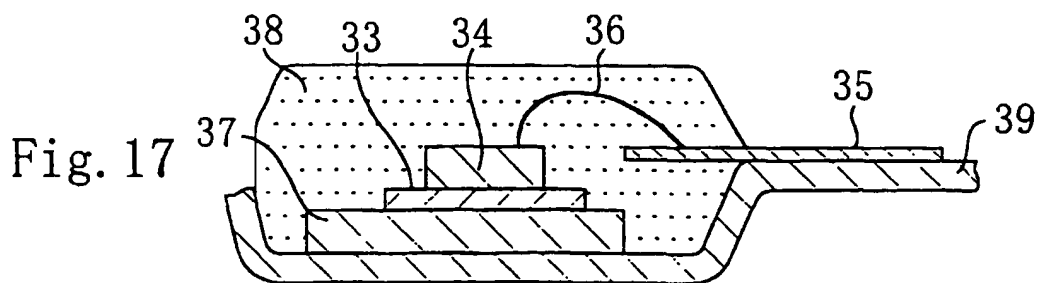
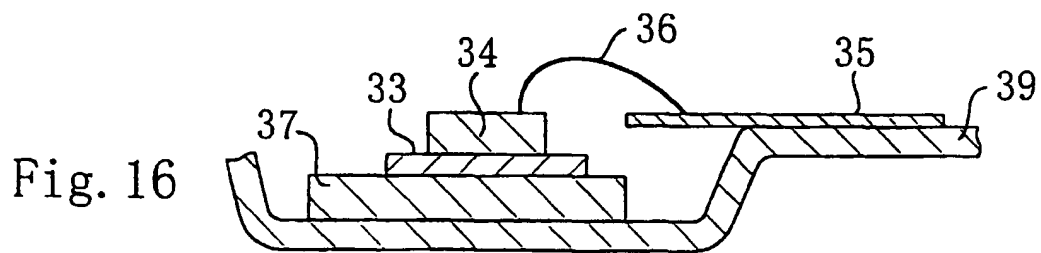
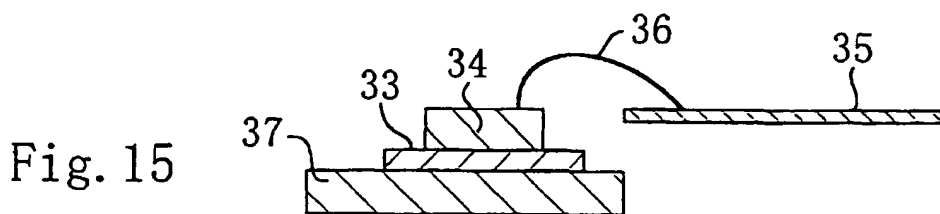
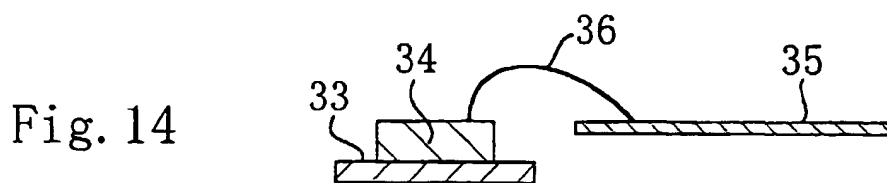
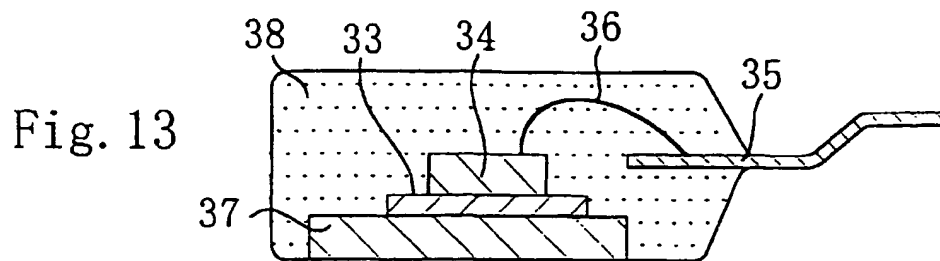


Fig. 12



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Fig. 18

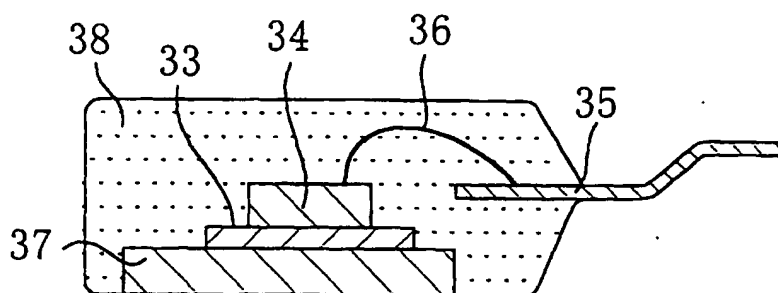
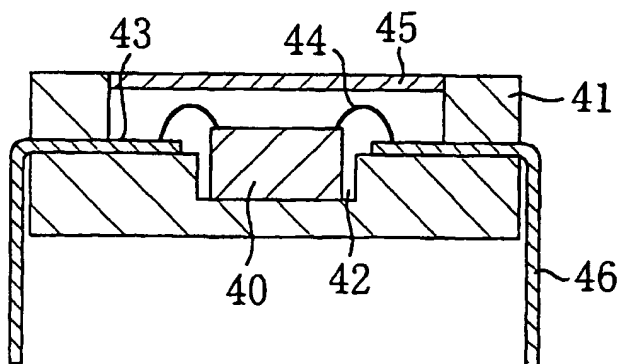
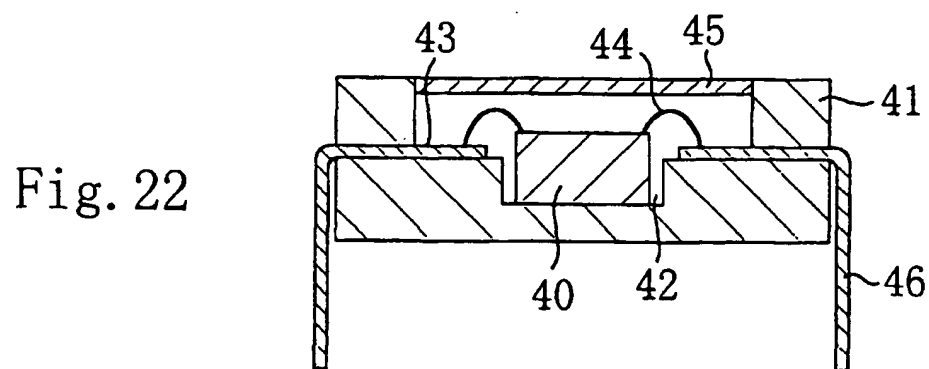
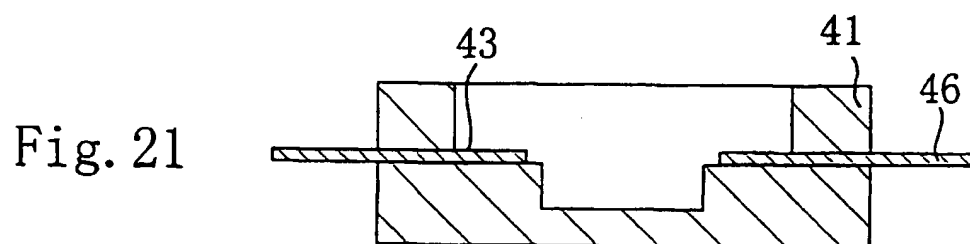
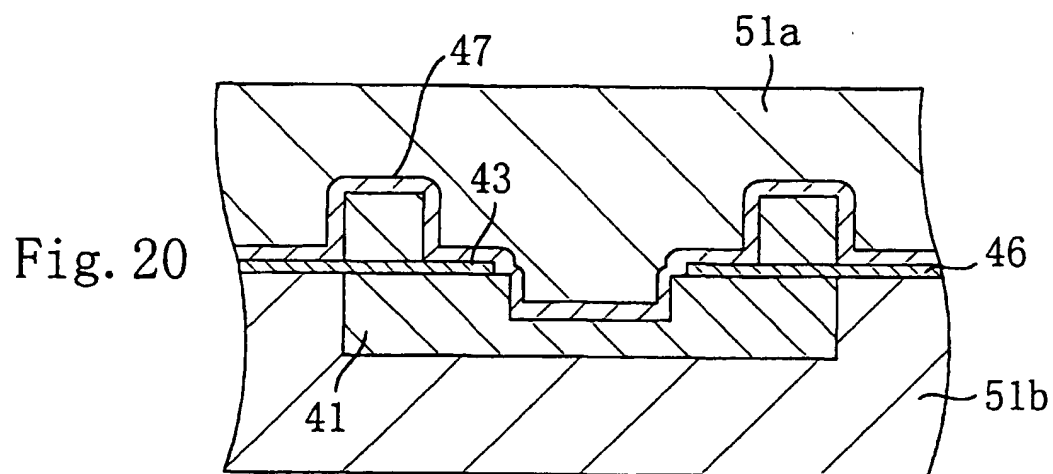


Fig. 19



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Fig. 23(a)

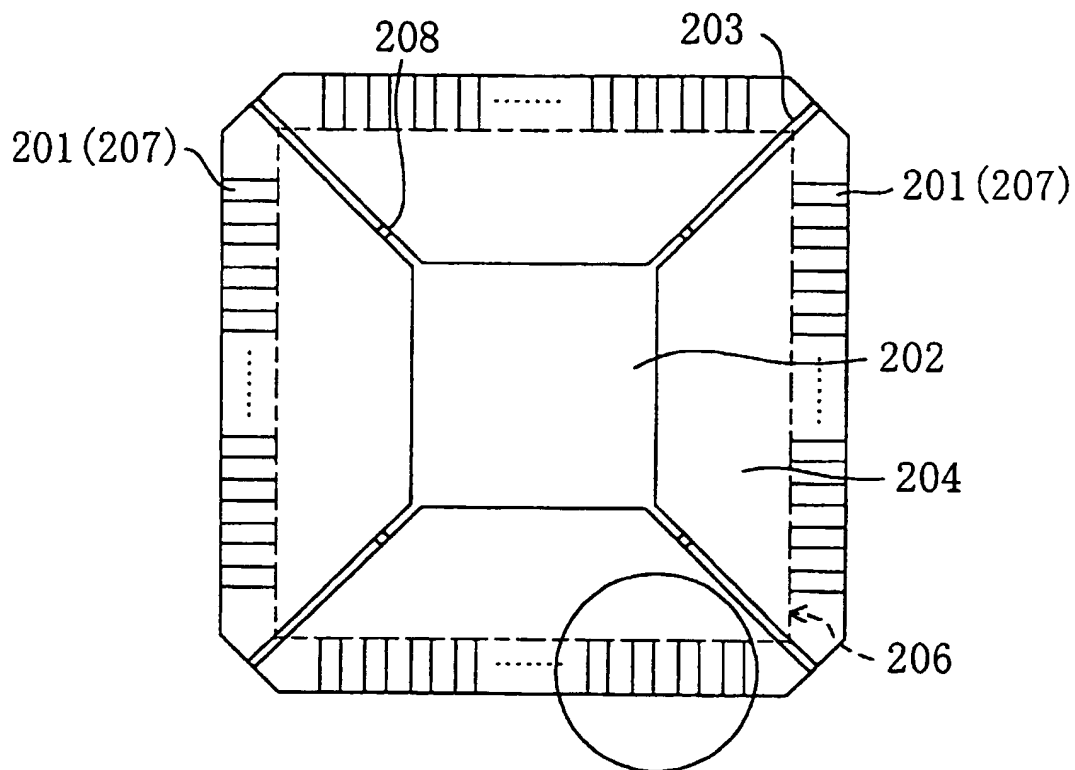
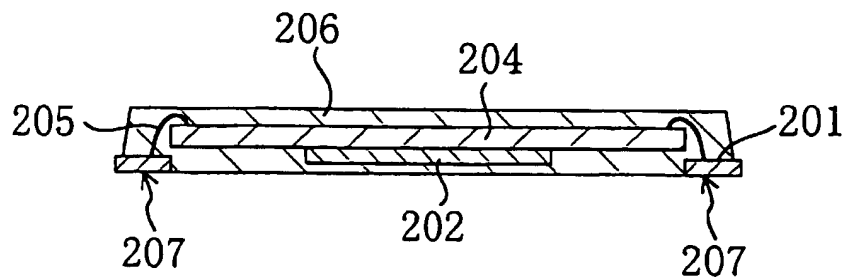


Fig. 23(b)



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Fig. 24

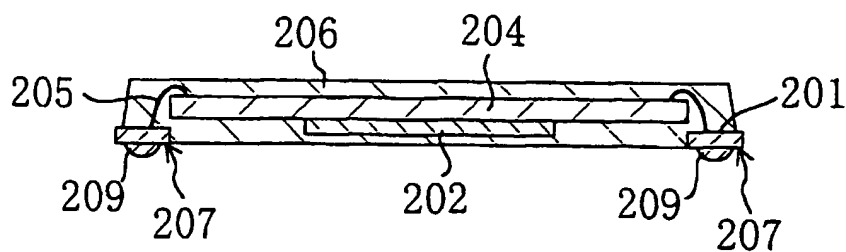


Fig. 25

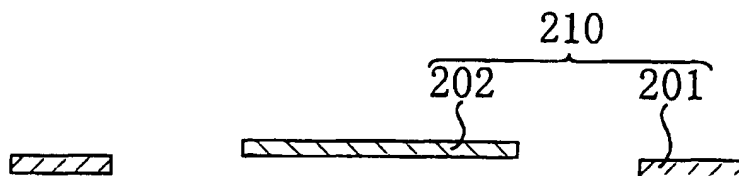


Fig. 26

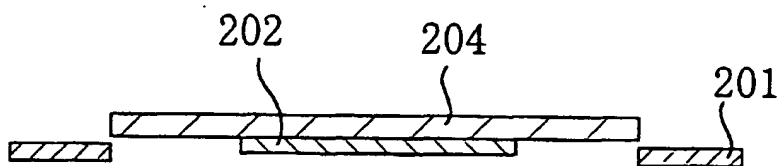


Fig. 27

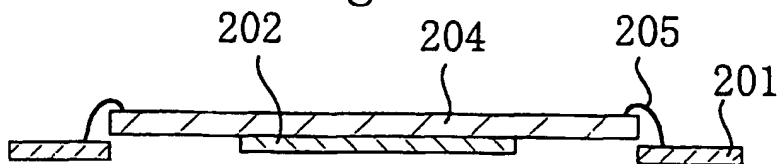
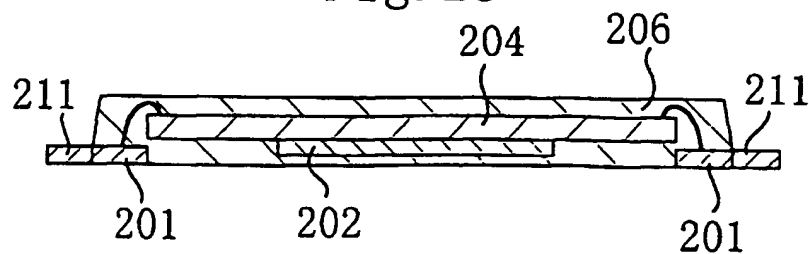


Fig. 28



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Fig. 29

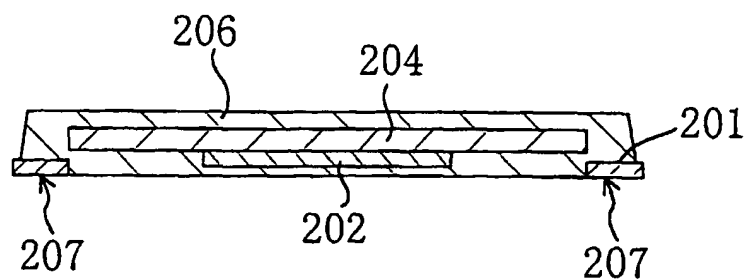
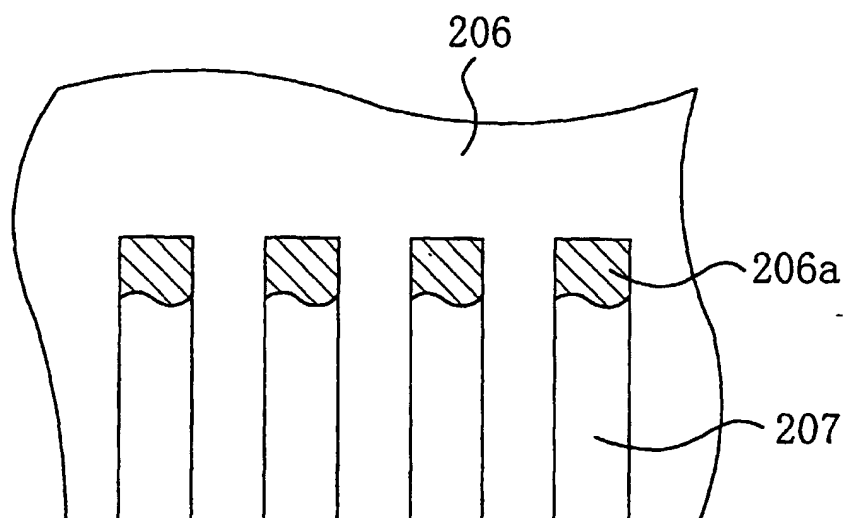


Fig. 30



INTERNATIONAL SEARCH REPORT

International application No.

PCT/JP98/00476

A. CLASSIFICATION OF SUBJECT MATTER Int.Cl. ⁶ H01L21/56, 23/28, 23/48, 23/12, 23/043 According to International Patent Classification (IPC) or to both national classification and IPC		
B. FIELDS SEARCHED Minimum documentation searched (classification system followed by classification symbols) Int.Cl. ⁶ H01L21/56, 23/28, 23/48, 23/12, 23/043 Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched Jitsuyo Shinan Koho 1926-1996 Toroku Jitsuyo Shinan Koho 1994-1998 Kokai Jitsuyo Shinan Koho 1971-1995 Jitsuyo Shinan Toroku Koho 1996-1998 Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)		
C. DOCUMENTS CONSIDERED TO BE RELEVANT		
Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X Y	JP, 5-47954, A (Toshiba Corp.), February 26, 1993 (26. 02. 93), Column 2, line 35 to column 3, line 5 ; Figs. 1, 2 (Family: none)	1 3
X Y	JP, 57-176751, A (Tokyo Shibaura Electric Co., Ltd.), October 30, 1982 (30. 10. 82), Page 2, upper right column, line 9 to page 3, upper left column, line 6 ; Figs. 2 to 4 (Family: none)	2 6
X	JP, 3-94459, A (Shinko Electric Industries Co., Ltd.), April 19, 1991 (19. 04. 91), Page 4, lower right column, line 6 to page 5, upper left column, line 17 ; Fig. 4 (Family: none)	4
<input checked="" type="checkbox"/> Further documents are listed in the continuation of Box C. <input type="checkbox"/> See patent family annex.		
* Special categories of cited documents: "A" document defining the general state of the art which is not considered to be of particular relevance "E" earlier document but published on or after the international filing date "L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified) "O" document referring to an oral disclosure, use, exhibition or other means "P" document published prior to the international filing date but later than the priority date claimed	"T" later document published after the international filing date or priority date and not in conflict with the application but cited to underpin the principle or theory underlying the invention "X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone "Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art "Z" document member of the same patent family	
Date of the actual completion of the international search April 30, 1998 (30. 04. 98)		Date of mailing of the international search report May 12, 1998 (12. 05. 98)
Name and mailing address of the ISA/ Japanese Patent Office		Authorized officer
Facsimile No.		Telephone No.

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INTERNATIONAL SEARCH REPORT

International application No.

PCT/JP98/00476

C (Continuation). DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	JP, 3-240260, A (Matsushita Electric Industrial Co., Ltd.),	5, 7
Y	October 25, 1991 (25. 10. 91),	6, 8
A	Page 1, lower right column, line 17 to page 2, upper left column, line 10 ; Figs. 4, 5 (Family: none)	9
Y	JP, 4-337657, A (Hitachi Cable, Ltd.),	8
	November 25, 1992 (25. 11. 92),	
	Column 4, lines 5 to 9 (Family: none)	
Y	JP, 2-133943, A (Contraves AG.),	10
	May 23, 1990 (23. 05. 90),	
	Page 7, upper left column, line 7 to lower right column, line 2 ; Figs. 3A to 3E	
	& EP, 351581, A1	
Y	JP, 2-134832, A (Seiko Epson Corp.),	10
	May 23, 1990 (23. 05. 90),	
	Page 2, upper left column, line 9 to upper right column, line 8 ; Figs. 1, 2 (Family: none)	
Y	JP, 2-122555, A (Mitsui High-tec, Inc.),	11-13
	May 10, 1990 (10. 05. 90),	
	Page 2, lower left column, line 4 to page 3, upper left column, line 11 ; Figs. 1 to 3 (Family: none)	
Y	JP, 52-67966, A (Tokyo Shibaura Electric Co., Ltd.),	11, 12
	June 6, 1977 (06. 06. 77),	
	Page 1, lower right column, line 16 to page 2, upper left column, line 2 ; Figs. 1 to 3 (Family: none)	
Y	JP, 60-50354, B2 (Matsushita Electronics Industry Corp.),	13
	November 8, 1985 (08. 11. 85),	
	Column 3, line 28 to column 4, line 24 ; Figs. 2, 3 (Family: none)	
X	JP, 2-209739, A (Mitsui Petrochemical Industries, Ltd.),	14
	August 21, 1990 (21. 08. 90),	
	Page 2, lower right column, line 13 to page 4, upper right column, line 15 ; Figs. 1, 2 (Family: none)	

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